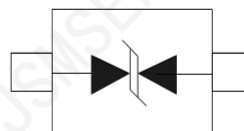


## Features

- 320Watts peak pulse power ( $t_p = 8/20\mu s$ )
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC 61000-4-2  $\pm 30kV$  contact  $\pm 30kV$  air
- IEC 61000-4-4 (EFT) 40A(5/50ns)
- IEC 61000-4-5 (Lightning) 10A(8/20 $\mu s$ )



SOD-323

## Applications

- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Pagers Peripherals

## Mechanical Data

- SOD323 package
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

## Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p = 8/20\mu s$ )	$P_{PP}$	320	Watts
Peak Pulse Current ( $t_p = 8/20\mu s$ ) (note1)	$I_{pp}$	10	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	$V_{ESD}$	30 30	kV
Lead Soldering Temperature	$T_L$	260(10seconds)	$^{\circ}C$
Junction Temperature	$T_J$	-55 to + 150	$^{\circ}C$
Storage Temperature	$T_{stg}$	-55 to + 150	$^{\circ}C$

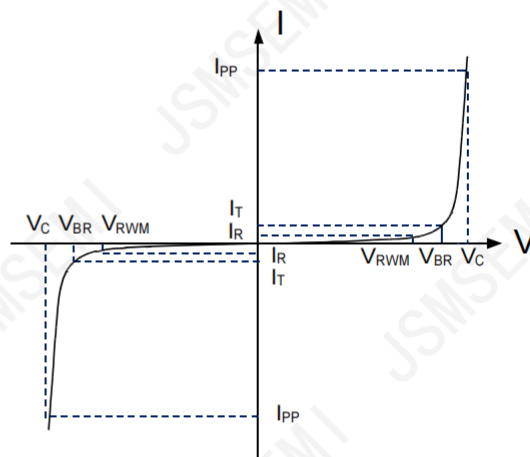
## Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$				15.0	V
Reverse Breakdown Voltage	$V_{BR}$	$I_T=1mA$	16.7			V
Reverse Leakage Current	$I_R$	$V_{RWM}=15V, T=25^{\circ}C$			0.5	$\mu A$
Clamping Voltage	$V_C$	$I_{PP}=10A, t_p=8/20\mu s$			32	V
Junction Capacitance	$C_j$	$V_R = 0V, f = 1MHz$		20		pF

## Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current

Note: 8/20 $\mu s$  pulse waveform.



## Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

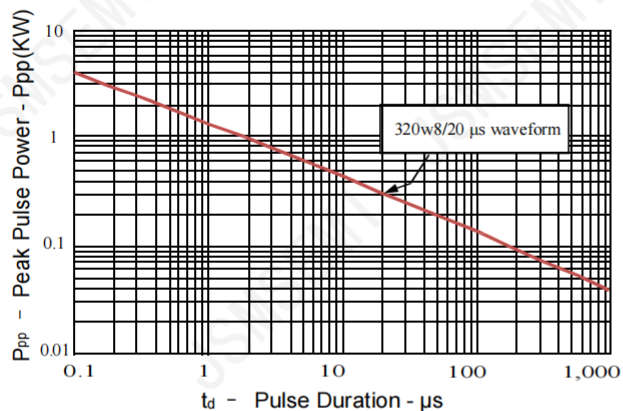


Figure 2: Power Derating Curve

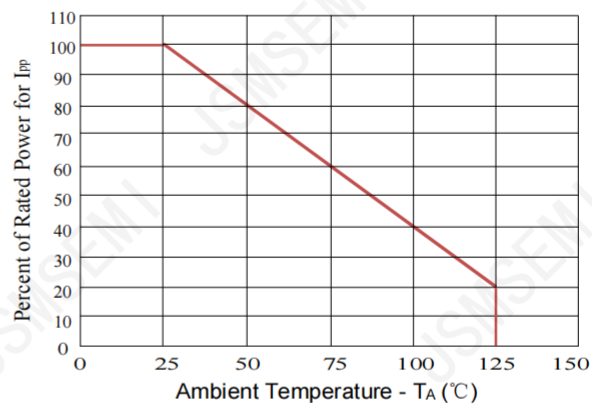


Figure3: Pulse Waveform

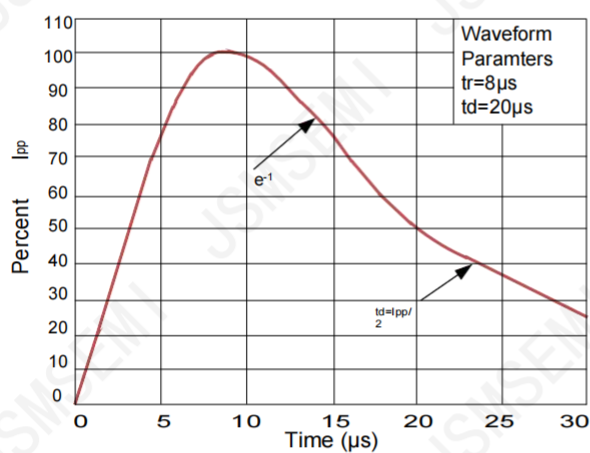
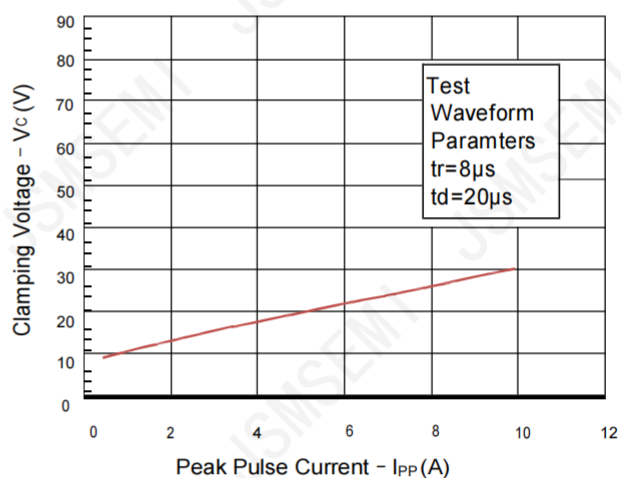
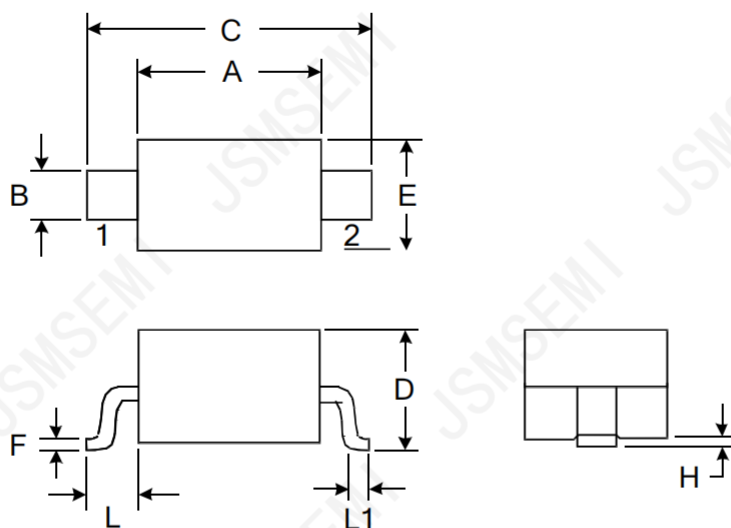


Figure 4: Clamping Voltage vs. Ipp



## Outline Drawing – SOD323



DIMENSIONS				
SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	1.600	1.800	0.063	0.071
B	0.250	0.350	0.010	0.014
C	2.500	2.700	0.098	0.106
D		1.000		0.039
E	1.200	1.400	0.047	0.055
F	0.080	0.150	0.003	0.006
L	0.475 REF		0.019REF	
L1	0.250	0.400	0.010	0.016
H	0.000	0.100	0.000	0.004

## Revision History

Rev.	Change	Date
V1.0	Initial version	2/23/2024

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